



PTO/SB/08A (07-05)

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**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

(Use as many sheets as necessary)

Complete if Known

Application Number	10/799838
Filing Date	Mar 12, 2004
First Named Inventor	Randy Hoffman
Art Unit	2814
Examiner Name	Long Pham
Attorney Docket Number	200316548-1

Sheet 1 of 2

U. S. PATENT DOCUMENTS

Examiner Initials*	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code ² (if known)			
LP		US-2004/0023432	02-05-2004	Haga	
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FOREIGN PATENT DOCUMENTS

Examiner Initials*	Cite No. ¹	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages Or Relevant Figures Appear	T ⁶
		Country Code ³ Number ⁴ Kind Code ⁵ (if known)				
LP		JP 2003-086808	03-20-2003	Kawasaki		

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Signature

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Date
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5/14/06

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Filing Date	Mar 12, 2004
First Named Inventor	Randy Hoffman
Art Unit	2814
Examiner Name	Long Pham
Attorney Docket Number	200316548-1

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		Document Number	Publication Date MM-DD-YYYY		
LP		US- Number/Kind Code ² # Inventor			
		5,744,864	04-28-1998	Cillessen	
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PATENT APPLICATION

Sheet 2 of 6

FORM PTO-1449

LIST OF PATENTS AND PUBLICATIONS FOR
APPLICANT'S INFORMATION DISCLOSURE
STATEMENT

(Use several sheets if necessary)

ATTY. DOCKET NO.

200316548-1

APPLICATION NO.

CONFIRMATION NO.

APPLICANT

Randy L. Hoffman, et al.

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REFERENCE DESIGNATION

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	PUBLICATION DATE	NAME	Pages, Columns, Lines Where Relevant Passages or Figures Appear
	2A			
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	2L				
	2M				
	2N				
	2O				
	2P				

OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)

LP	2Q	Fu, Shelton, et al., "MOS and MOSFET with Transistion Metal Oxides", SPIE Vol. 2897, pp. 520-527.
	2R	Giesbers, J.B., et al., "Dry Etching of All-Oxide Transparent Thin Film Memory Transistors", Microelectronic Engineering, Vol. 35, pp. 71-74 (1997).
	2S	Grosse-Holz, K.O., et al. "Semiconductive Behavior of Sb Doped SnO2 Thin Films", Mat. Res. Soc. Symp. Proc., Vol. 401, pp. 67-72 (1996).

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	3L					
	3M					
	3N					
	3O					
	3P					

OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, etc.)

LP	3Q	Hoffman, R.L., et al., "ZnO-based transparent thin-film transistors", Applied Physics Letters, Vol. 82, No. 5, pp. 733-735 (February 3, 2003).
↓	3R	Masuda, Satoshi, et al., "Transparent thin film transistors using ZnO as an active channel layer and their electrical properties", Journal of Applied Physics, Vol. 93, No. 3, pp. 1824-1830 (February 1, 2003).
↓	3S	Nishi, Junya, et al., "High Mobility Thin Film Transistors with Transparent ZnO Channels", Jpn. J. Appl. Phys., Vol. 42, Part 2, No. 4A, pp. L347-L349 (April, 2003).

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PATENT APPLICATION

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	4L				
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	4N				
	4O				
	4P				

OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)

LP ↓	4Q	Ohya, Yutaka, et al., "Thin Film Transistor of ZnO Fabricated by Chemical Solution Deposition", Jpn. J. Appl. Phys., Vol. 40, Part 1, No. 1, pp. 297-298 (January, 2001).
	4R	Pellecchi, Ilaria, et al. "SrTiO3-based metal-insulator-semiconductor heterostructures" Applied Physics Letters, Vol. 78, No. 15, pp. 2244-2246 (April 9, 2001).
	4S	Prins, M. W. J., et al., "A ferroelectric transparent thin-film transistor", Appl. Phys. Lett., Vol. 68, No. 25, pp. 3650-3652 (June 17, 1996).

EXAMINER

Long PHAM

DATE CONSIDERED

12/6/05

PATENT APPLICATION
Sheet 6 of 6

FORM PTO-1449 LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)	ATTY. DOCKET NO. 200316548-1	APPLICATION NO.	CONFIRMATION NO.
APPLICANT Randy L. Hoffman, et al.			
FILING DATE Herewith		GROUP	

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	8L				
	8M				
	8N				
	8O				
	8P				

OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, etc.)

LP	8Q	Yoshida, A., "Three Terminal Field Effect Superconducting Device Using SrTiO3 Channel" IEEE Transactions on Applied Superconductivity, Vol. 5, No. 2, pp. 2892-2895 (June, 1995).
↓	8R	Solid-State Electronics, Vol. 7, Pergamon Press, Notes pp. 701-702 (1964).
✓	8S	Anonymous, "Transparent and/or memory thin film transistors in LCD's and PLEAD," Research Disclosure, p. 890 (July 1998).

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	5L				
	5M				
	5N				
	5O				
	5P				

OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, etc.)

LP	5Q	Seager, C.H., et al., "Charge Trapping and device behavior in ferroelectric memories", Appl. Phys. Lett., Vol. 68, No. 19, pp. 2660-2662 (May 6, 1996).
	5R	Uneno, K., et al. "Field-effect transistor on SrTiO ₃ with sputtered Al ₂ O ₃ gate insulator", Applied Physics Letters, Vol. 83, No. 9, pp. 1755-1757 (September 1, 2003).
	5S	Wöllenstein, Jürgen, et al., "An insulated gate thin-film transistor using SnO ₂ as semiconducting channel, a possible new gas sensor device" The 11th European Conference on Solid State Transducers, pp. 471-474 (September 21-24, 1997).

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